6 Channel EMI Filter Array with ESD Protection

Features

- Six channels of EMI filtering for data ports
- Pi-style EMI filters in a capacitor-resistor-capacitor (C-R-C) network
- Greater than 32dB attenuation at 1GHz
- ±15kV ESD protection on each channel (IEC 61000-4-2 Level 4, contact discharge)
- ±30kV ESD protection on each channel (HBM)
- Chip Scale Package features extremely low lead inductance for optimum filter and ESD performance
- 15-bump, 2.960mm X 1.330mm footprint Chip Scale Package (CSP)
- Lead-free version available

Applications

- EMI filtering and ESD protection for both data and I/O ports
- Wireless Handsets
- Handheld PCs / PDAs
- MP3 Players
- Notebooks
- Desktop PCs

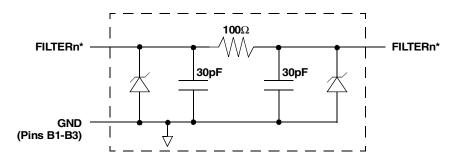
Product Description

The CSPEMI306A is a six channel low-pass filter array that reduces EMI/RFI emissions while at the same time providing ESD protection. It is used on data ports on mobile devices. To reduce EMI/RFI emissions, the CSPEMI306A integrates a pi-style filter (C-R-C) for each of the 6 channels. Each high quality filter provides greater than 30dB attenuation in the 800-2700 MHz range. These pi-style filters also support bidirectional filtering, controlling EMI both to and from a data port connector.

In addition, the CSPEMI306A provides a very high level of protection for sensitive electronic components that may be subjected to electrostatic discharge (ESD). The input pins are designed and characterized to safely dissipate ESD strikes of 15kV, exceeding the maximum requirement of the IEC 61000-4-2 international standard. Using the MIL-STD-883 (Method 3015) specification for Human Body Model (HBM) ESD, the device provides protection for contact discharges to greater than 30kV.

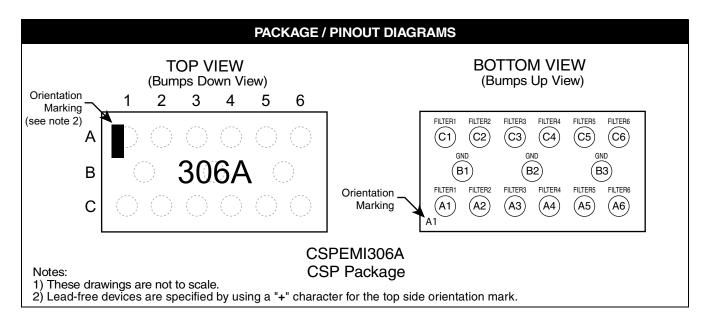
The CSPEMI306A is particularly well suited for portable electronics (e.g., cellular telephones, PDAs, notebook computers) because of its small package footprint and low weight. The CSPEMI306A is available in a space-saving, low-profile Chip Scale Package with optional lead-free finishing.

Electrical Schematic



1 of 6 EMI/RFI + ESD Channels

^{*} See Package/Pinout Diagram for expanded pin information.



	PIN DESCRIPTIONS					
PIN(s)	NAME	DESCRIPTION				
A1	FILTER1	Filter Channel 1				
A2	FILTER2	Filter Channel 2				
А3	FILTER3	Filter Channel 3				
A4	FILTER4	Filter Channel 4				
A5	FILTER5	Filter Channel 5				
A6	FILTER6	Filter Channel 6				
B1-B3	GND	Device Ground				
C1	FILTER1	Filter Channel 1				
C2	FILTER2	Filter Channel 2				
С3	FILTER3	Filter Channel 3				
C4	FILTER4	Filter Channel 4				
C5	FILTER5	Filter Channel 5				
C6	FILTER6	Filter Channel 6				

Ordering Information

PART NUMBERING INFORMATION							
		Standa	rd Finish	Lead-free Finish ²			
		Ordering Part		Ordering Part			
Bumps	Package	Number ¹	Part Marking	Number ¹	Part Marking		
15	CSP	CSPEMI306A	306A	CSPEMI306AG	306A		

Note 1: Parts are shipped in Tape & Reel form unless otherwise specified.

Note 2: Lead-free devices are specified by using a "+" character for the top side orientation mark.

Specifications

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	RATING	UNITS			
Storage Temperature Range	-65 to +150	°C			
DC Power per Resistor	100	mW			
DC Package Power Rating	600	mW			

STANDARD OPERATING CONDITIONS						
PARAMETER	RATING	UNITS				
Operating Temperature Range	-40 to +85	°C				

	ELECTRICAL C	PERATING CHARAC	CTERIS	STICS	1	
SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
R	Resistance		80	100	120	Ω
С	Capacitance	At 2.5V DC	24	30	36	pF
TCR	Temperature Coefficient of Resistance			1200		ppm/°C
TCC	Temperature Coefficient of Capacitance	At 2.5V DC		-300		ppm/°C
V _{DIODE}	Diode Voltage (reverse bias)	I _{DIODE} =10μA	5.5			V
I _{LEAK}	Diode Leakage Current (reverse bias)	V _{DIODE} =3.3V			100	nA
V _{SIG}	Signal Voltage Positive Clamp Negative Clamp	I _{LOAD} = 10mA	5.6 -0.4	6.8 -0.8	9.0 -1.5	V V
V _{ESD}	In-system ESD Withstand Voltage a) Human Body Model, MIL-STD-883, Method 3015 b) Contact Discharge per IEC 61000-4-2 Level 4	Notes 2,4 and 5	±30 ±15			kV kV
V _{CL}	Clamping Voltage during ESD Discharge MIL-STD-883 (Method 3015), 8kV Positive Transients Negative Transients	Notes 2,3,4 and 5		+10 -5		V
f _C	Cut-off frequency $Z_{SOURCE} = 50\Omega$, $Z_{LOAD} = 50\Omega$	R = 100Ω , C = $30pF$		58		MHz

Note 1: $T_A=25$ °C unless otherwise specified.

Note 2: ESD applied to input and output pins with respect to GND, one at a time.

Note 3: Clamping voltage is measured at the opposite side of the EMI filter to the ESD pin. For example, if ESD is applied to Pin A1, then clamping voltage is measured at Pin C1.

Note 4: Unused pins are left open

Note 5: These parameters are guaranteed by design and characterization.

Performance Information

Typical Filter Performance (T_A=25°C, DC Bias=0V, 50 Ohm Environment)

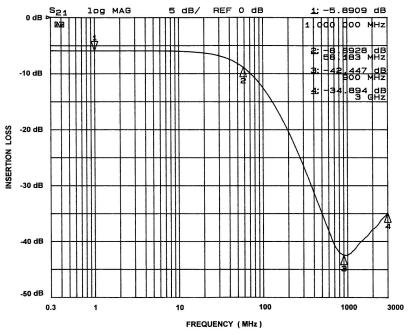


Figure 1. Insertion Loss VS. Frequency (A1-C1 to GND B2)

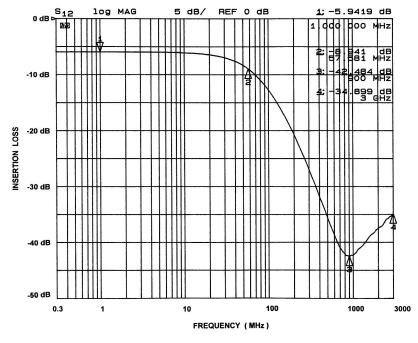


Figure 2. Insertion Loss VS. Frequency (A2-C2 to GND B2)

Typical Filter Performance (T_A=25°C, DC Bias=0V, 50 Ohm Environment)

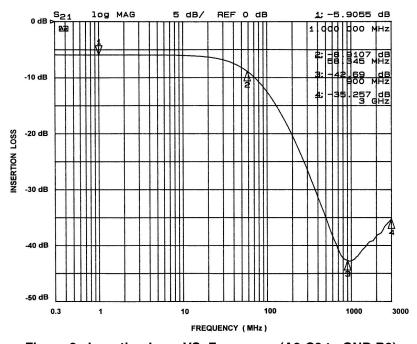


Figure 3. Insertion Loss VS. Frequency (A3-C3 to GND B2)

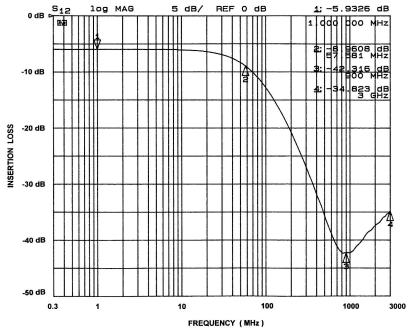


Figure 4. Insertion Loss VS. Frequency (A4-C4 to GND B2)

Typical Filter Performance (T_A=25°C, DC Bias=0V, 50 Ohm Environment)

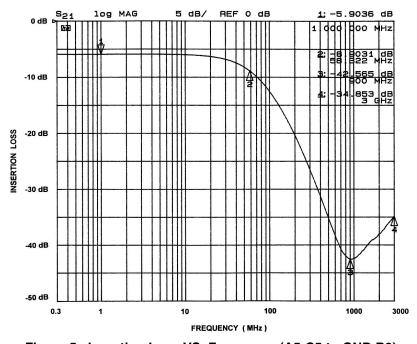


Figure 5. Insertion Loss VS. Frequency (A5-C5 to GND B2)

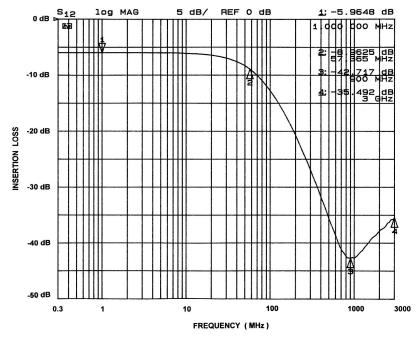


Figure 6. Insertion Loss VS. Frequency (A6-C6 to GND B2)

Typical Filter Performance (T_A=25°C, DC Bias=0V, 50 Ohm Environment)

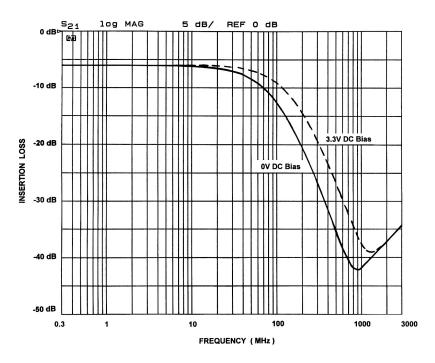


Figure 7. Comparison of Filter Response Curves for CSPEMI306A VS. DC Bias

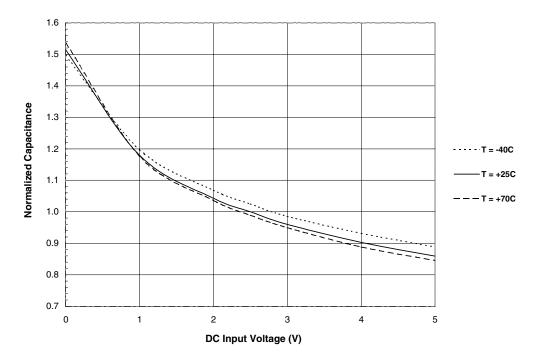


Figure 8. Filter Capacitance vs. Input Voltage over Temperature (normalized to capacitance at 2.5VDC and 25°C)

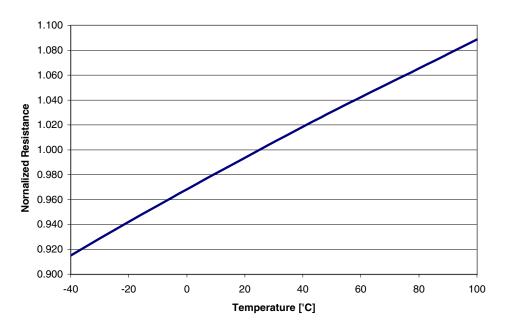


Figure 9. Resistance vs. Temperature (normalized to resistance at 25°C)

Application Information

Refer to Application Note AP-217, "The Chip Scale Package", for a detailed description of Chip Scale Packages offered by California Micro Devices.

PRINTED CIRCUIT BOARD RECOMMENDATIONS					
PARAMETER	VALUE				
Pad Size on PCB	0.275mm				
Pad Shape	Round				
Pad Definition	Non-Solder Mask defined pads				
Solder Mask Opening	0.325mm Round				
Solder Stencil Thickness	0.125 - 0.150mm				
Solder Stencil Aperture Opening (laser cut, 5% tapered walls)	0.330mm Round				
Solder Flux Ratio	50/50 by volume				
Solder Paste Type	No Clean				
Pad Protective Finish	OSP (Entek Cu Plus 106A)				
Tolerance — Edge To Corner Ball	<u>±</u> 50μm				
Solder Ball Side Coplanarity	±20μm				
Maximum Dwell Time Above Liquidous	60 seconds				
Soldering Maximum Temperature	260°C				

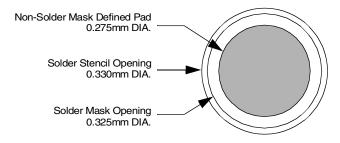


Figure 10. Recommended Non-Solder Mask Defined Pad Illustration

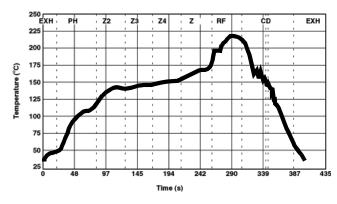


Figure 11. Eutectic (SnPb) Solder Ball Reflow Profile

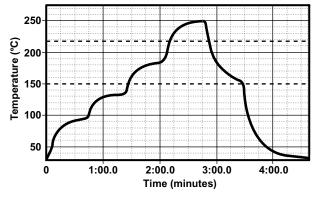


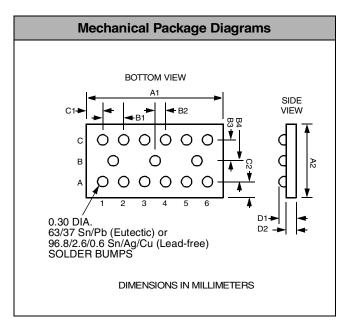
Figure 12. Lead-free (SnAgCu) Solder Ball Reflow Profile

Mechanical Details

CSP Mechanical Specifications

CSPEMI306A devices are packaged in a custom Chip Scale Package (CSP). Dimensions are presented below. For complete information on CSP packaging, see the California Micro Devices CSP Package Information document.

PACKAGE DIMENSIONS							
Pack	age	Custom CSP					
Bumps		15					
Dim	Millimete		rs	rs Inches			
Dilli	Min	Nom	Max	Min	Nom	Max	
A1	2.915	2.960	3.005	0.1148	0.1165	0.1183	
A2	1.285	1.330	1.375	0.0506	0.0524	0.0541	
B1	0.495	0.500	0.505	0.0195	0.0197	0.0199	
B2	0.245	245 0.250 0.255 0.0096		0.0096	0.0098	0.0100	
В3	0.430	0.435	0.440	0.0169	0.0171	0.0173	
B4	0.430	0.435	0.440	0.0169 0.017		0.0173	
C1	0.180	0.230	0.280	0.0071	0.0091	0.0110	
C2	0.180	0.230	0.280	0.0071	0.0091	0.0110	
D1	0.561	0.605	0.605 0.649		0.0238	0.0255	
D2	0.355	0.380	0.405	0.0140	0.0150	0.0159	
# per tape and reel		3500 pieces					
Controlling dimension: millimeters							



Package Dimensions for CSPEMI306A Chip Scale Package

CSP Tape and Reel Specifications

PART NUMBER	CHIP SIZE (mm)	POCKET SIZE (mm) B ₀ X A ₀ X K ₀	TAPE WIDTH W	REEL DIAMETER	QTY PER REEL	P ₀	P ₁
CSPEMI306A	2.96 X 1.33 X 0.6	3.10 X 1.45 X 0.74	8mm	178mm (7")	3500	4mm	4mm

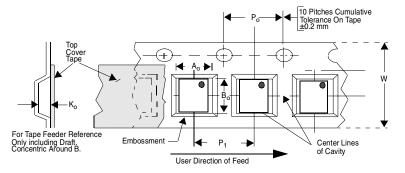


Figure 13. Tape and Reel Mechanical Data